

DBP and C₇₀ Based Inverted Tandem Solar Cells Using Simple Interconnecting Layer

Supporting Information

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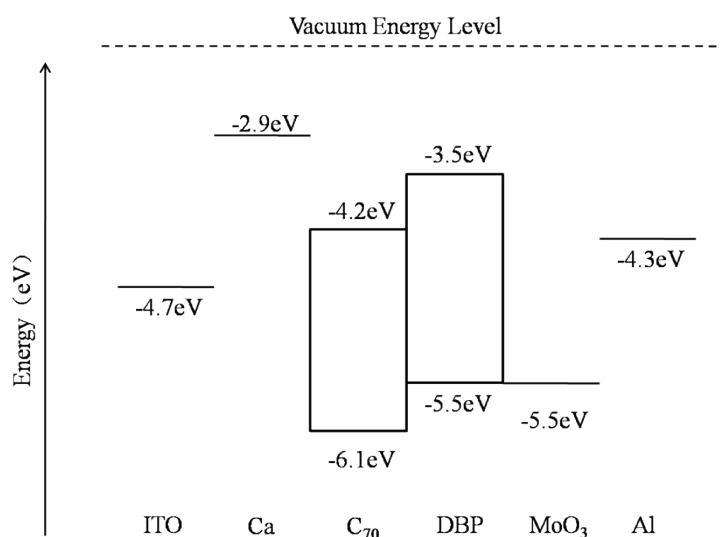


Fig. SI 1 Energy level diagram of inverted structure cells.

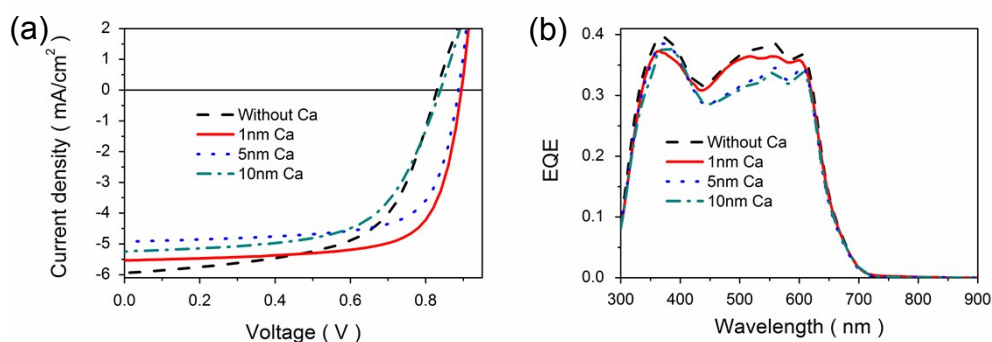


Fig. SI 2 (a) *J-V* curves of inverted structure cells with different Ca thickness under simulated AM1.5G solar illumination at 100 mW/cm². (b) EQE spectra of inverted structure cells with different Ca thickness. Device structure: ITO/Ca(X nm)/C₇₀(40 nm)/DBP(20 nm)/MoO₃(5 nm

)/Al.

Table SI 1 Photovoltaic performances with different Ca thickness.

Device structure: ITO/Ca(X nm)/C₇₀(40 nm)/DBP(20 nm)/MoO₃(5 nm)/Al.

Ca (nm)	J_{sc} (mA/cm ²)	V_{oc} (V)	FF (%)	PCE%
0	5.95	0.83	60	2.97
1	5.56	0.89	73	3.59
5	4.93	0.89	71	3.09
10	5.24	0.84	62	2.73

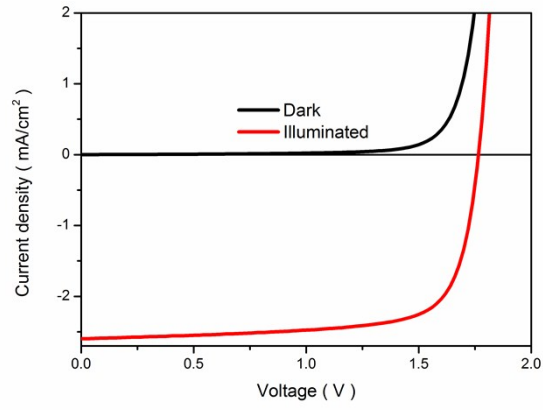


Fig. SI 3 J - V curves of tandem structure cells with different acceptors in front and rear cells under simulated AM1.5G solar illumination at 100 mW/cm².